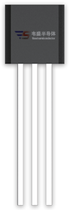
MPSA13 TRANSISTOR (NPN)

FEATURES

- Darlington Transistors


TO-92

1.EMITTER

2.COLLECTOR

3.BASE

ORDERING INFORMATION

Part Number	Package	Packing Method	Pack Quantity
MPSA13	TO-92	Bulk	1000pcs/Bag
MPSA13-TA	TO-92	Tape	2000pcs/Box

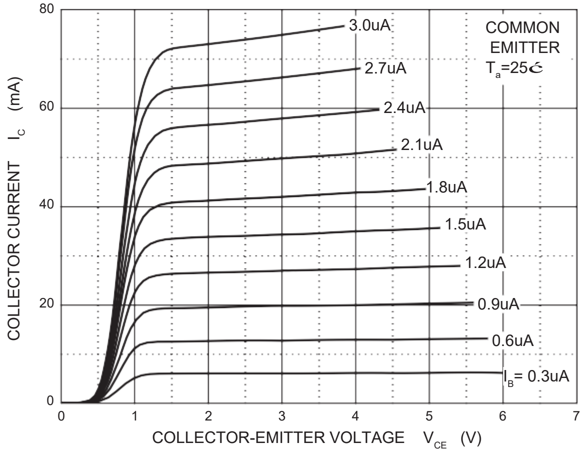
MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	30	V
V_{CEO}	Collector-Emitter Voltage	30	V
V_{EBO}	Emitter-Base Voltage	10	V
I_C	Collector Current -Continuous	0.5	A
P_D	Collector Power Dissipation	625	mW
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	200	℃ /W
T_J,T_{stg}	Operation Junction and Storage Temperature Range	-55~+150	℃

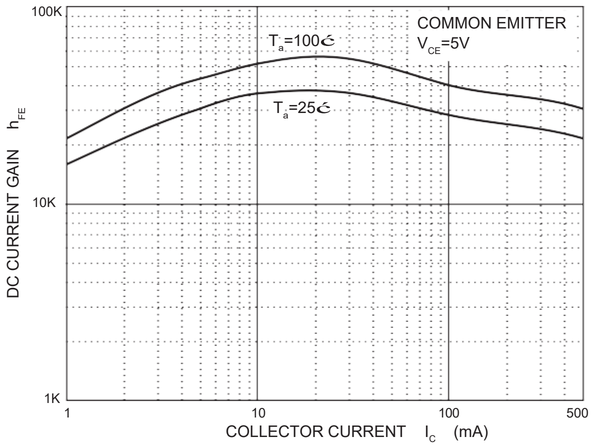
T_a=25℃ unless otherwise specified

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C= 0.1mA,I_E=0	30			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=1mA,I_B=0	30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=0.1mA,I_C=0	10			V
Collector cut-off current	I_{CBO}	V_{CB}=30V,I_E=0			0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=10V,I_C=0			0.1	μA
DC current gain	$h_{FE(1)}$*	V_{CE}=5V, I_C=10mA	5000			
	$h_{FE(2)}$*	V_{CE}=5V, I_C=100mA	10000			
Collector-emitter saturation voltage	$V_{CE(sat)}$*	I_C=100mA,I_B=0.1mA			1.5	V
Base-emitter voltage	V_{BE}*	V_{CE}=5V,I_C=100mA			2.0	V
Current gain-bandwidth product	f_T	V_{CE}=5V,I_C=10mA,f=100MHz	125			MHz

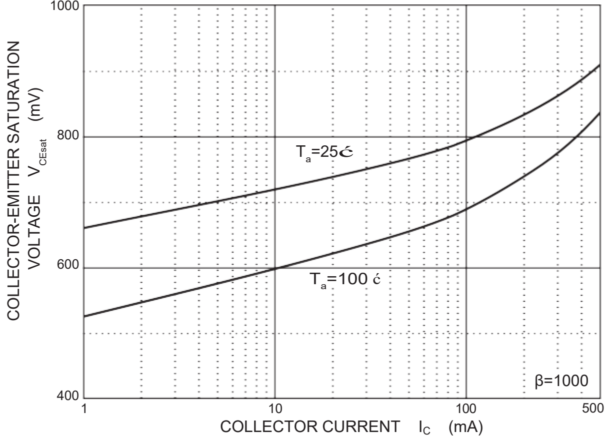
*Pulse test: pulse width ≤300μs, duty cycle≤ 2.0%.



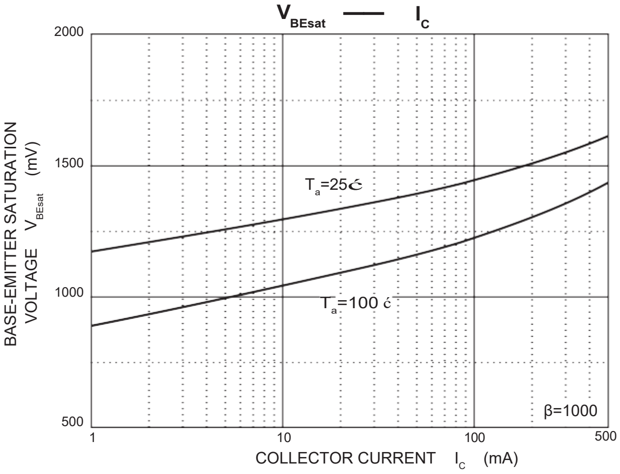
Static Characteristic



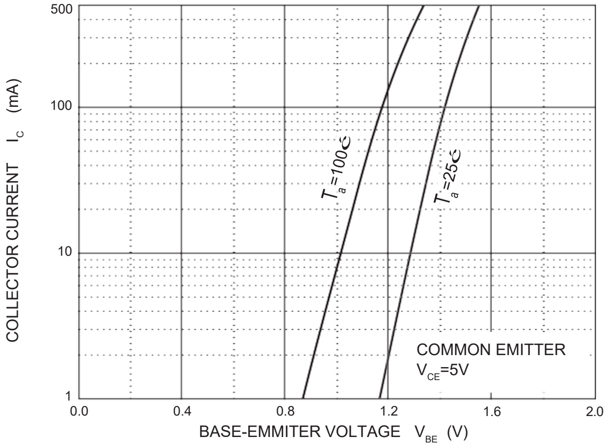
h_{FE} — I_C



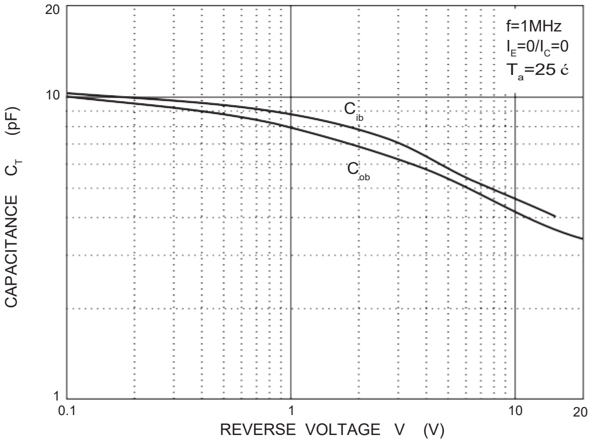
V_{CEsat} — I_C



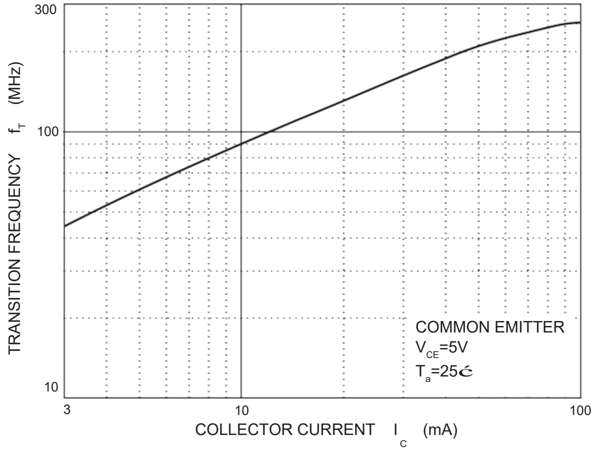
V_{BEsat} — I_C



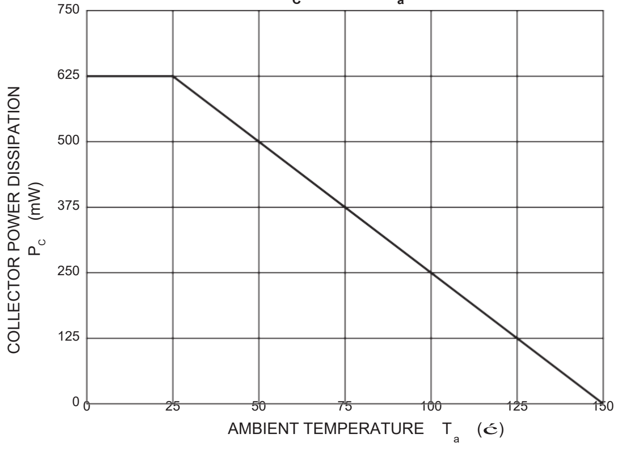
I_C — V_{BE}



C_{ob}/C_{ib} — V_{CB}/V_{EB}



f_T — I_C



P_C — T_a